Unit in mm

#### TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

# 2SC2782A

#### VHF BAND POWER AMPLIFIER APPLICATIONS

• Output Power : Po = 80W (Min.)

 $(f = 175MHz, V_{CC} = 12.5V, P_{i} = 18W)$ 

# **ABSOLUTE MAXIMUM RATINGS (Tc = 25°C)**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	36	V
Collector-Emitter Voltage	V <sub>CEO</sub>	16	V
Emitter-Base Voltage	V <sub>EBO</sub>	4	٧
Collector Current	IC	20	Α
Collector Power Dissipation	PC	220	W
Junction Temperature	Tj	175	°C
Storage Temperature Range	T <sub>stg</sub>	-65~175	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba

Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

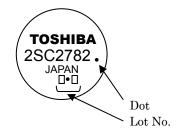
### $18.4 \pm 0.5$ 3.9±0. -ø3.2 (( 5.2±0.3 3 68±07 7.5±0.3 $18.4 \pm 0.2$ $24.6 \pm 0.5$ **EMITTER** 4. EMITTER 2. **EMITTER** 5. **EMITTER** COLLECTOR BASE 6. **JEDEC**

2-13C1A

TOSHIBA Weight: 5.5g

**EIAJ** 

#### **MARKING**

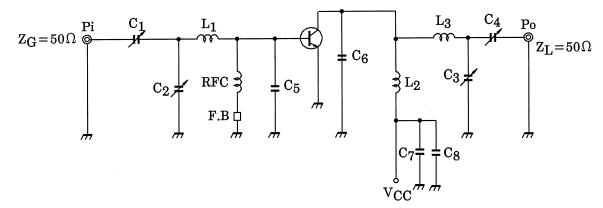


# ELECTRICAL CHARACTERISTICS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	V (BR) CBO	I <sub>C</sub> = 20mA, I <sub>E</sub> = 0	36	_	_	V
Collector-Emitter Breakdown Voltage	V (BR) CEO	I <sub>C</sub> = 50mA, I <sub>B</sub> = 0	16	_	_	٧
Emitter-Base Breakdown Voltage	V (BR) EBO	I <sub>E</sub> = 1mA, I <sub>C</sub> = 0	4	_	_	V
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10A *	10	_	_	
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 12.5V, I <sub>E</sub> = 0 f = 1MHz	_	_	320	pF
Output Power	Po	(Fig.) V <sub>CC</sub> = 12.5V, f = 175MHz	80	90	_	W
Power Gain	Gp		6.4	6.8	_	dB
Collector Efficiency	ηс	Pi = 18W	60	70	_	%
Series Equivalent Input Impedance	Z <sub>in</sub>	V <sub>CC</sub> = 12.5V	_	1.0 +j1.5	_	Ω
Series Equivalent Output Impedance	Z <sub>out</sub>	f = 175MHz, Po = 80W	_	1.2 +j1.8	_	Ω

<sup>\*</sup> Pulse Test: Pulse Width ≤ 100µs, Duty Cycle ≤ 3%

## Fig. Po TEST CIRCUIT



 $C_1 \sim C_4 : \sim 20 pF$ 

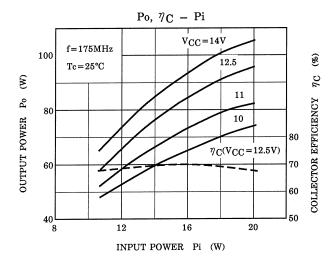
 $C_5$  : 156pF (39pF $\times$ 4) CERAMIC CONDENSER  $C_6$  : 132pF (33pF $\times$ 4) CERAMIC CONDENSER

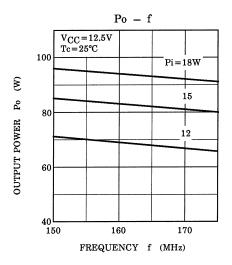
 $_{\rm C_7}$  :  $0.01 \mu {
m F}$  CERAMIC CONDENSER

 $C_8$  :  $10\mu F$ 

L<sub>1</sub>, L<sub>3</sub> :  $\phi$ 1.5mm SILVER PLATED COPPER WIRE, 10ID, 1T L<sub>2</sub> :  $\phi$ 1.5mm SILVER PLATED COPPER WIRE, 10ID, 2T RFC :  $\phi$ 1mm ENAMEL COATED COPPER WIRE, 6ID, 10T

FB : FERRITE BEAD





#### **CAUTION**

These are only typical curves and devices are not necessarily guaranteed at these curves.

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2007-11-01

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20070701-EN GENERAL

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